MCH3476

Power MOSFET 20V, $125m\Omega$, 2A, Single N-Channel



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Features

- Low On-Resistance
- 1.8V Drive
- ESD Diode-Protected Gate
- Pb-Free, Halogen Free and RoHS Compliance

VDSS	KDS(OII) Max	יט Max
	125mΩ@ 4.5V	
20V	190mΩ@ 2.5V	2A
	310mΩ@ 1.8V	

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Specifications

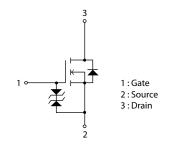
Absolute Maximum Ratings at Ta = 25°C

Parameter	Symbol	Value	Unit
Drain to Source Voltage	V _{DSS}	20	V
Gate to Source Voltage	V _{GSS}	±12	V
Drain Current (DC)	ID	2	Α
Drain Current (Pulse) PW≤10μs, duty cycle≤1%	I _{DP}	8	А
Power Dissipation When mounted on ceramic substrate (900mm² × 0.8mm)	PD	0.8	W
Junction Temperature	Tj	150	°C
Storage Temperature	Tstg	–55 to +150	°C

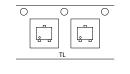
Thermal Resistance Ratings

5					
Parameter	Symbol	Value	Unit		
Junction to Ambient					
When mounted on ceramic substrate	$R_{\theta JA}$	156.2	°C/W		
(900mm ² × 0.8mm)					

Electrical Connection N-Channel



Packing Type : TL Marking





Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

ORDERING INFORMATION

See detailed ordering and shipping information on page 5 of this data sheet.

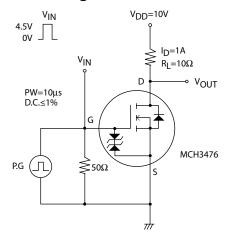
MCH3476

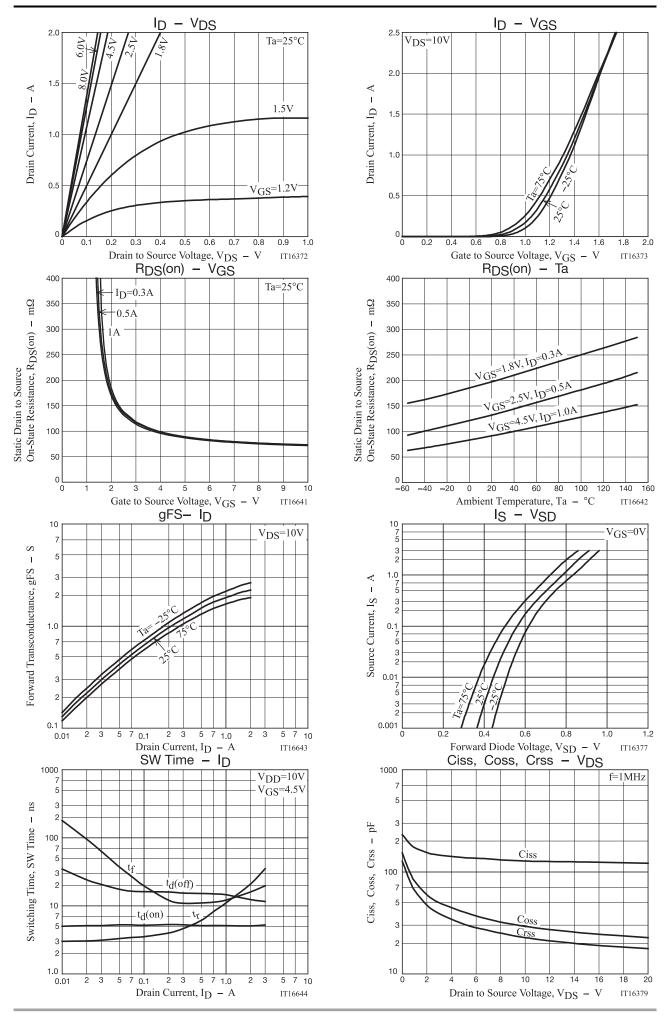
Electrical Characteristics at Ta = 25°C

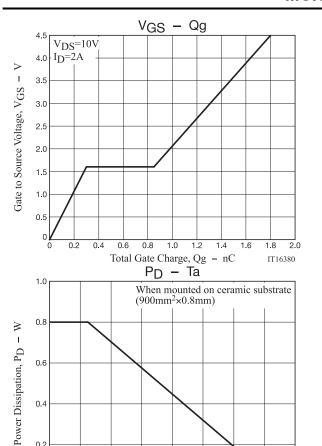
Parameter	Symbol	Conditions	Value			l locit
Parameter			min	typ	max	Unit
Drain to Source Breakdown Voltage	V(BR)DSS	I _D =1mA, V _{GS} =0V	20			٧
Zero-Gate Voltage Drain Current	I _{DSS}	V _{DS} =20V, V _{GS} =0V			1	μΑ
Gate to Source Leakage Current	IGSS	V _{GS} =±8V, V _{DS} =0V			±10	μΑ
Gate Threshold Voltage	V _{GS} (th)	V _{DS} =10V, I _D =1mA	0.4		1.3	V
Forward Transconductance	9FS	V _{DS} =10V, I _D =1A		1.9		S
	R _{DS} (on)1	I _D =1A, V _{GS} =4.5V		93	125	mΩ
Static Drain to Source On-State Resistance	R _{DS} (on)2	I _D =0.5A, V _{GS} =2.5V		135	190	mΩ
	R _{DS} (on)3	I _D =0.3A, V _{GS} =1.8V		200	310	mΩ
Input Capacitance	Ciss			128		pF
Output Capacitance	t Capacitance Coss	V _{DS} =10V, f=1MHz		28		pF
Reverse Transfer Capacitance	Crss			21		pF
Turn-ON Delay Time	t _d (on)			5.1		ns
Rise Time Turn-OFF Delay Time	t _r	See specified Test Circuit		11		ns
	t _d (off)			14.5		ns
Fall Time	t _f			12		ns
Total Gate Charge	Qg			1.8		nC
Gate to Source Charge	Qgs	V _{DS} =10V, V _{GS} =4.5V, I _D =2A		0.3		nC
Gate to Drain "Miller" Charge	Qgd	1		0.55		nC
Forward Diode Voltage	V _{SD}	I _S =2A, V _{GS} =0V		0.85	1.2	V

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

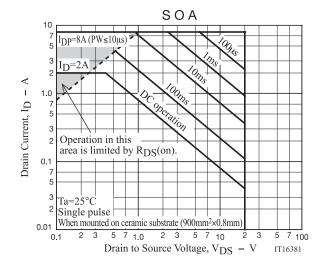
Switching Time Test Circuit

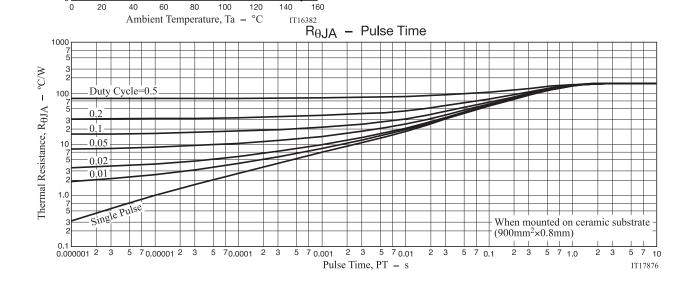






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Package Dimensions

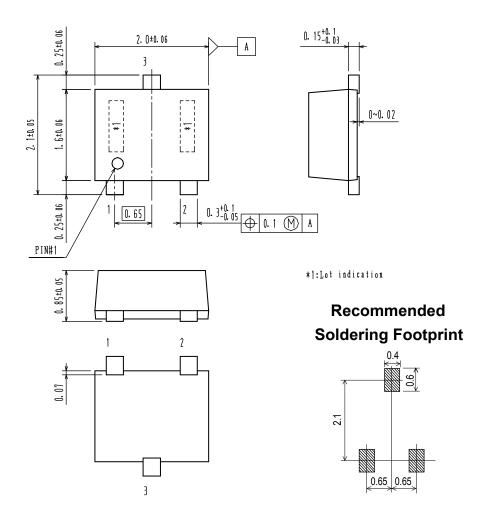
MCH3476-TL-H / MCH3476-TL-W

MCPH3

CASE 419AQ ISSUE O

unit: mm

1 : Gate 2 : Source 3 : Drain



ORDERING INFORMATION

Device	Package	Shipping	Note	
MCH3476-TL-H	MCPH3 SC-70FL, SOT-323	3,000 pcs. / Tape & Reel	Pb-Free	
MCH3476-TL-W		3,000 pcs. / Tape & Reel	and Halogen Free	

[†] For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D. http://www.onsemi.com/pub_link/Collateral/BRD8011-D.PDF

Note on usage: Since the MCH3476 is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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